Title (en)

RADIATION-EMITTING SEMICONDUCTOR BODY WITH CARRIER SUBSTRATE AND METHOD FOR THE PRODUCTION THEREOF

Title (de)

STRAHLUNGSEMITTIERENDER HALBLEITERKÖRPER MIT TRÄGERSUBSTRAT UND VERFAHREN ZUR HERSTELLUNG EINES SOLCHEN

Title (fr)

CORPS SEMI-CONDUCTEUR ÉMETTEUR DE RAYONNEMENT AVEC UN SUBSTRAT DE SUPPORT ET SON PROCÉDÉ DE FABRICATION

Publication

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Application

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Abstract (en)

[origin: WO2007124737A1] The invention relates to a radiation-emitting semiconductor body with carrier substrate and a method for the production thereof. The method involves producing a structured connection of a semiconductor layer sequence (2) to a carrier substrate wafer (1). The semiconductor layer sequence is subdivided into a plurality of semiconductor layer stacks (200) by means of cuts (6) through the semiconductor layer sequence and the carrier substrate wafer (1) is subdivided into a plurality of carrier substrates (100) by means of cuts (7) through the carrier substrate wafer (1). In this case, the structured connection is embodied in such a way that at least one semiconductor layer stack (200) is connected to precisely one associated carrier substrate (100). Moreover, at least one cut (7) through the carrier substrate wafer is lengthened by none of the cuts (6) through the semiconductor layer sequence in such a way that a rectilinear cut through the carrier substrate wafer and the semiconductor layer sequence results.

IPC 8 full level

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